L Number	Hits	Search Text	DB	Time stamp
Number	184659	encapsulat\$ or passivat\$	USPAT;	2002/10/22
			US-PGPUB;	15:09
			EPO; JPO;	
i	1		DERWENT;	
2	2503	hangaqual abutana ar hah	IBM_TDB USPAT;	2002/10/22
2	2503	benzocyclobutene or bcb	US-PGPUB;	15:10
			EPO; JPO;	10.10
			DERWENT;	
			IBM_TDB	
ⁱ 3	5773877	1 •	USPAT;	2002/10/22
		titanium	US-PGPUB; EPO; JPO;	15:11
			DERWENT;	
			IBM TDB	
4	422101	cure\$1 or curing	USPĀT;	2002/10/22
1			US-PGPUB;	15:12
			EPO; JPO;	
			DERWENT; IBM TDB	
5	379534	planar\$	USPAT;	2002/10/22
	0.3001		US-PGPUB;	15:12
		, (EPO; JPO;	
		L.	DERWENT;	
	20		IBM_TDB	2002/10/20
6	20	<pre>(encapsulat\$ or passivat\$) same (benzocyclobutene or bcb) same (cure\$1 or</pre>	USPAT;	2002/10/22 15:13
!		curing)	US-PGPUB; EPO; JPO;	15:15
		Calling	DERWENT;	
			IBM TDB	
17	5	(Committee of the comm	USPAT;	2002/10/22
		(benzocyclobutene or bcb) same (cure\$1 or	US-PGPUB;	15:24
		curing)) and (pt or platinum or au or gold or ti or titanium) and planar\$	EPO; JPO; DERWENT;	
1		gold of the thankoun, and planary	IBM TDB	1
9	390590	planar\$ or etch\$3 adj2 back or etchback\$	USPAT;	2002/10/22
			US-PGPUB;	15:27
			EPO; JPO;	
			DERWENT;	
11	1257280	expos\$5	IBM_TDB USPAT;	2002/10/22
11	1237200	caposys	US-PGPUB;	15:29
			EPO; JPO;	
			DERWENT;	
1.2	1.630	(mlaman) an ababés adés troit ou	IBM_TDB	2002/10/22
12	1630	<pre>(planar\$ or etch\$3 adj2 back or etchback\$) same expos\$5 same (pt or</pre>	USPAT; US-PGPUB;	2002/10/22 15:30
		platinum or au or gold or ti or titanium)	EPO; JPO;	13.30
		goad of the carried	DERWENT;	
			IBM_TDB	
13	9240	(encapsulat\$ or passivat\$) same (cure\$1	USPAT;	2002/10/22
•		or curing)	US-PGPUB;	15:30
1			EPO; JPO; DERWENT;	
			IBM TDB	
14	27		USPAT;	2002/10/22
		etchback\$) same expos\$5 same (pt or	US-PGPUB;	15:47
		platinum or au or gold or ti or	EPO; JPO;	
		titanium)) and ((encapsulat\$ or	DERWENT;	
15	20	<pre>passivat\$) same (cure\$1 or curing)) (encapsulat\$ or passivat\$) same</pre>	IBM_TDB USPAT;	2002/10/22
	1	(benzocyclobutene or bcb) same (cure\$1 or	US-PGPUB;	15:49
		curing)	EPO; JPO;	
			DERWENT;	
l			IBM_TDB	

	Retrieval Classif	Inventor	S	С	P	2	3	4	5
1		Goo, Ju-seon et al.	\boxtimes						
2		Adrian, Ng Choon Seng	\boxtimes						
3		Sachdev, Krishna Gandhi et al.	×						
4		Ng, Choon Seng Adrian	\boxtimes						
5		Teong, Jennifer Su Ping	\boxtimes						
6		Carey, David H.	×						
7		YASUDA, HIDEFUMI et al.	\boxtimes						
8		Yoshimura, Tetsuzo et al.	\boxtimes						
9		Anagnostopoulos, Constantine N. et al.	×						
10		Bai, Jinchuan	\boxtimes						
11		Yoshimura, Tetsuzo et al.	\boxtimes						
12		Yoshimura, Tetsuzo et al.	×						

	I	mage Doc. Displayed	PT
1	US	5989983	
2	US	5977599	
3	US	5976710	
4	US	5843839	
5	US	5639692	
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7	JP A	2000012485	
8	US	20020097962	
9	US	20020067391	
10	US	20020047200	
11	US	20020039464	
12	US	20020028045	

	U	1 🗸	Document ID Issue Date	Pages
13			US 20020017702 A1	29
14			US 20020009860 A1	30
15			US 20010005044 A1	16
16			US 6343171 B1 20020129	94
17			US 6294830 B1 20010925	16
18			US 6093584 A 20000725	17
19			US 6001671 A 19991214	18
20			US 5874358 A 19990223	11
21			US 5619071 A 19970408	11
22			US 5474958 A 19951212	17

	Title	Current OR	Current XRef
13	Methods for manufacturing resistors using a sacrificial layer	257/536	
14	Methods for manufacturing resistors using a sacrificial layer	438/384	
15	Microelectronic assemblies having exposed conductive terminals and methods therefor	257/678	
16	Systems based on opto-electronic substrates with electrical and optical interconnections and methods for making	385/50	385/14; 385/18; 385/24
17	Microelectronic assembly with conductive terminals having an exposed surface through a dielectric layer	257/724	257/684; 257/730; 257/784; 257/786; 257/787
18	Method for encapsulating a semiconductor package having apertures through a sacrificial layer and contact pads	438/127	438/108; 438/110; 438/119; 438/124; 438/126
19	Methods for manufacturing a semiconductor package having a sacrificial layer	438/112	438/110; 438/126; 438/127
20	Via hole profile and method of fabrication	438/640	438/673; 438/701; 438/754
21	Anchored via connection	257/753	257/763; 257/764; 257/765; 257/774; 257/775; 257/915
22	Method for making semiconductor device having no die supporting surface	29/827	257/676; 257/778; 257/787; 29/841; 29/856; 438/118; 438/124; 438/126

	Retrieval Classif	Inventor	S	С	P	2	3	4	5
13		Fjelstad, Joseph	Ø						
14		Fjelstad, Joseph	\boxtimes						
15		Fjelstad, Joseph	\boxtimes						
16		Yoshimura, Tetsuzo et al.	×						
17		Fjelstad, Joseph	×						
18		Fjelstad, Joseph	\boxtimes						
19		Fjelstad, Joseph	×						
20		Myers, Alan M. et al.	×						
21		Myers, Alan M. et al.	\boxtimes						
22		Djennas, Frank et al.	\boxtimes						

	I	mage Doc. Displayed	PT
13	US	20020017702	
14	US	20020009860	
15	US	20010005044	
16	US	6343171	
17	US	6294830	
18	US	6093584	
19	US	6001671	
20	US	5874358	
21	US	5619071	
22	US	5474958	

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23			US 5470790 A	19951128	11
24			US 5091339 A	19920225	34
25			US 3996066 A	19761207	14
26			NN9304335	19930401	1
27			NA82123336	19821201	1

	Title	Current OR	Current XRef
23	Via hole profile and method of fabrication	438/625	257/774; 438/640; 438/666; 438/672; 438/673; 438/688; 438/701
24	Trenching techniques for forming vias and channels in multilayer electrical interconnects	216/18	216/48; 430/312; 438/623; 438/631; 438/940; 438/945
25	Lithium-iodine battery	429/185	29/623.2; 429/213; 607/9
26	Corrosion and Electromigration-Resistant High-Conductivity VLSI Interconnects		
27	Selective Activation of Metal Salt Loaded Polyimide by Exposure to Plasma. December 1982.		

	Retrieval Classif	Inventor	S	С	Р	2	3	4	5
23		Myers, Alan M. et al.	\boxtimes						
24		Carey, David H.	\boxtimes						
25		Mead, Ralph T. et al.	\boxtimes						
26			\boxtimes						
27			\boxtimes						

	Image Doc. Displayed	PT
23	US 5470790	
24	US 5091339	
25	US 3996066	
26	NN9304335	
27	NA82123336	

	U	1 🗸	D	ocument ID	Issue Date	Pages
1		\boxtimes	US	6294018 B1	20010925	12
2		⊠	US	6137125 A	20001024	6
3		X	US	6121689 A	20000919	22
4		X	US	5578226 A	19961126	8
5		X	US	5288989 A	19940222	6
6		\boxtimes	JР	10050720 A	19980220	9
7		×	US	6383916 B	20020507	17
8			US A1	20020118254	20020829	11
9			US A1	20020079458	20020627	35
10			US A1	20020020855	20020221	14
11			US A1	20020014703	20020207	18
12		,	US A1	20010012642	20010809	11

	Title	Current OR	Current XRef
1	Alignment techniques for epitaxial growth processes	117/90	117/94; 117/95; 117/954; 117/955; 117/96
2	Two layer hermetic-like coating for on-wafer encapsulatuon of GaAs MMIC's having flip-chip bonding capabilities	257/275	257/640; 257/778
3	Semiconductor flip-chip package and method for the fabrication thereof	257/783	257/773; 257/778; 257/787
4	Multi-layered superconductive interconnects	216/33	216/101; 216/88; 505/410; 505/820
5	Avalanche photodiode with moisture resistant passivation coating disposed to cover the outer periphery of the photodiode body except at a selected top contact area	250/214.1	250/208.1; 257/186
6	MANUFACTURE OF SEMICONDUCTOR DEVICE		
7	Metallic laminate formation, for integrated circuit, involves forming multilayered metallic laminate having metal lines of width greater than metal lines of metallization structure on polyamide layer		
8	Interconnected printhead die and carrier substrate system	347/50	347/40 ; 347/44
9	Hybrid detector for X-ray imaging	250/370.11	
10	Method for fabricating a semiconductor device	257/200	
11	Semiconductor flip-chip package and method for the fabrication thereof	257/778	438/107
12	Flip-chip package with optimized encapsulant adhesion and method	438/107	438/109

	Retrieval Classif	Inventor	S	С	P	2	3	4	5
1		Hamm, Robert Alan et al.	\boxtimes						
2		Costas, Varmazis D. et al.	\boxtimes						
3		Capote, Miguel A. et al.	Ø						
4		Chan, Hugo W. et al.	\boxtimes						
5		Ishaque, A. Nadeem et al.	\boxtimes						
6		YAMAHATA, SHIYOUJI	\boxtimes						
7		LIN, M	\boxtimes						
8		Wong, Marvin G. et al.	\boxtimes						
9		Zur, Albert	\boxtimes						
10		Hwang, Chan Seung	\boxtimes						
11		Capote, Miguel A. et al.	\boxtimes						
12		Kodnani, Ramesh R. et al.	\boxtimes						

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1	US	6294018				
2	US	6137125				
3	US	6121689				
4	US	5578226				
5	US	5288989				
6	JР	10050720 A				
7	US	6383916				
8	US	20020118254				
9	US	20020079458				
10	US	20020020855				
11	US	20020014703				
12	US	20010012642				

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13			US	6466279	В1	20021015	11
1 4			US	6455408	B1	20020924	15
15			US	6297560	B1	20011002	17
16			US	6249039	B1	20010619	17
17			US	6248614	В1	20010619	10
18			US	6130693	A	20001010	10
19			US	5930438	Α	19990727	б
20			US	5232970	Α	19930803	10

	I	mage Doc. Displayed	PT
13	US	6466279	
14	US	6455408	
15	US	6297560	
16	US	6249039	
17	US	6248614	
18	US	6130693	
19	US		
20	US	5232970	

	Title	Current OR	Current XRef
13	Liquid crystal display device and process for producing same in which forming first and second organic insulating layers using curing and half curing process		349/122; 349/138; 349/158
14	Method for manufacturing semiconductor devices having redistribution patterns with a concave pattern in a bump pad area	438/613	438/612
1.5	Semiconductor flip-chip assembly with pre-applied encapsulating layers	257/778	257/701; 257/773; 257/777; 257/779; 257/780; 257/782; 257/783; 257/785; 257/786; 257/789; 257/795
16	Integrated inductive components and method of fabricating such components	257/531	257/528; 257/549; 438/329; 438/381
17	Flip-chip package with optimized encapsulant adhesion and method	438/107	438/108; 438/127; 520/1; 528/44
18	Ink jet printhead which prevents accumulation of air bubbles therein and method of fabrication thereof	347/65	
19	Method for manufacturing an optoelectrical component and an optoelectrical component manufactured according to the method	385/129	385/130; 385/131
20	Ceramic-filled thermally-conductive-composit es containing fusible semi-crystalline polyamide and/or polybenzocyclobutenes for use in microelectronic applications	524/404	523/443; 523/445; 523/451; 523/468; 524/414; 524/433; 524/443

	Retrieval Classif	Inventor	S	С	P	2	3	4	5
. 13		Nakata, Shinichi	\boxtimes						
14		Hwang, Chan Seung et al.	×						
15		Capote, Miguel A. et al.	\boxtimes						
16		Harvey, Ian Robert et al.	\boxtimes						
17		Kodnani, Ramesh R. et al.	\boxtimes						
18		Ims, Dale R. et al.	×						
19		Palmskog, Goran et al.	\boxtimes						
20		Solc, Jitka et al.	\boxtimes						